

Dual High-Voltage Schottky Rectifiers

REV:1.12

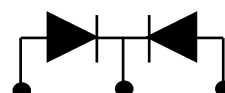
Product Character	◆ Half Bridge Rectified、Common Cathode Structure.
	◆ Multilayer Metal -Silicon Potential Structure.
	◆ Low Power Waste, High Efficiency.
	◆ Beautiful High Temperature Character.
	◆ Have Over Voltage protect loop, high reliability.
	◆ RoHs Product.

Typical Reference Data

VRRM= 100V

IF(AV)= 10A

Polarity



Primary Use	● Low Voltage High Frequency Switching Power Supply.
	● Low Voltage High Frequency Invers Circuit.
	● Low Voltage Continued Circuit and Protection Circuit.

Summarize	■ SR10100CS Schottky diode, in the manufacture uses the main process technology includes: Silicon epitaxial substrate, P+ loop technology, The potential metal and the silicon alloy technology, the device uses the two chip, the common cathode, the plastic half package structure.
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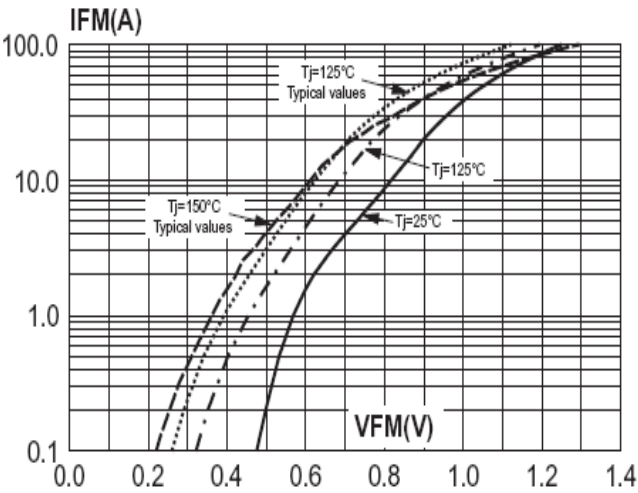
Absolute Maximum Ratings

Item	Symbol	SR10100CS	Unit
Maximal Inverted Repetitive Peak Voltage	VRRM	100	V
Maximal DC Interdiction Voltage	VDC	100	V
Average Rectified Forward Current TC=150℃ Whole Device	IFAV	10	A
		5	
Forward Peak Surge Current (Rated Load 8.3 Half Mssine Wave-According to JEDEC Method)	IFSM	125	A
Operating Junction Temperature	TJ	-40- +150	℃
Storage Temperature	TSTG	-40- +150	℃
Maximum Thermal Resistance Junction-to-Case	RθJC	4.0	℃/W

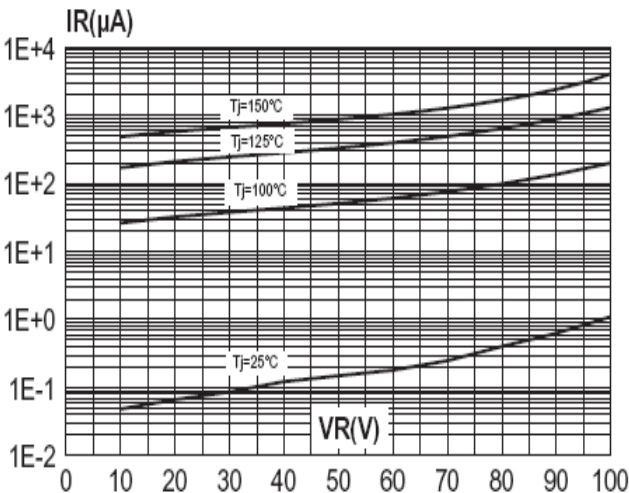
Electricity Character

Item	Test Condition		Minimum	Representative	Maximum	Unit
IR	TJ =25℃	VR=VRRM			20	uA
	TJ =125℃				1	mA
VF	TJ =25℃	IF=5A			0.80	V

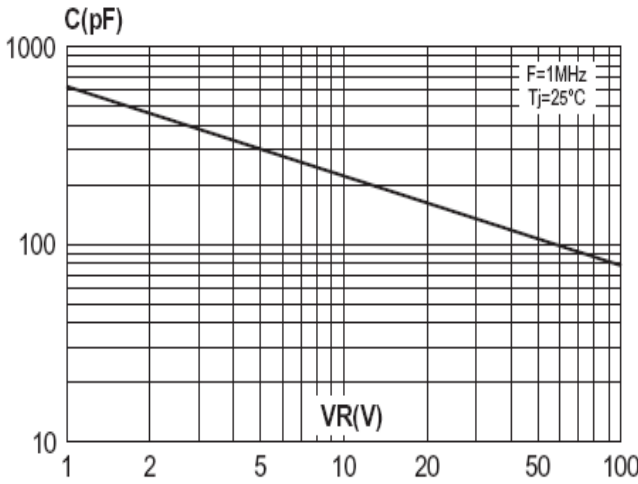
The forward voltage and forward current curve



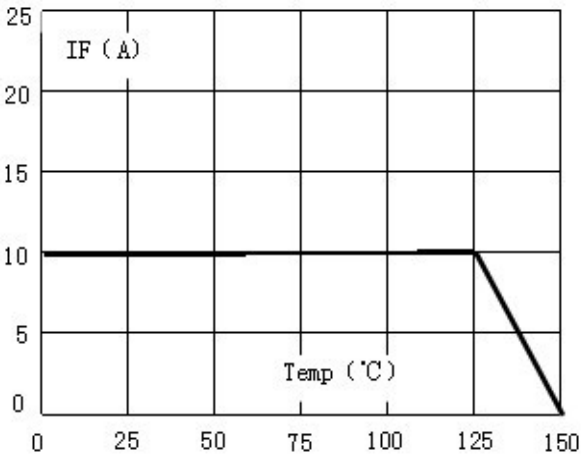
The reverse leak current and the reverse voltage (single-device) curve



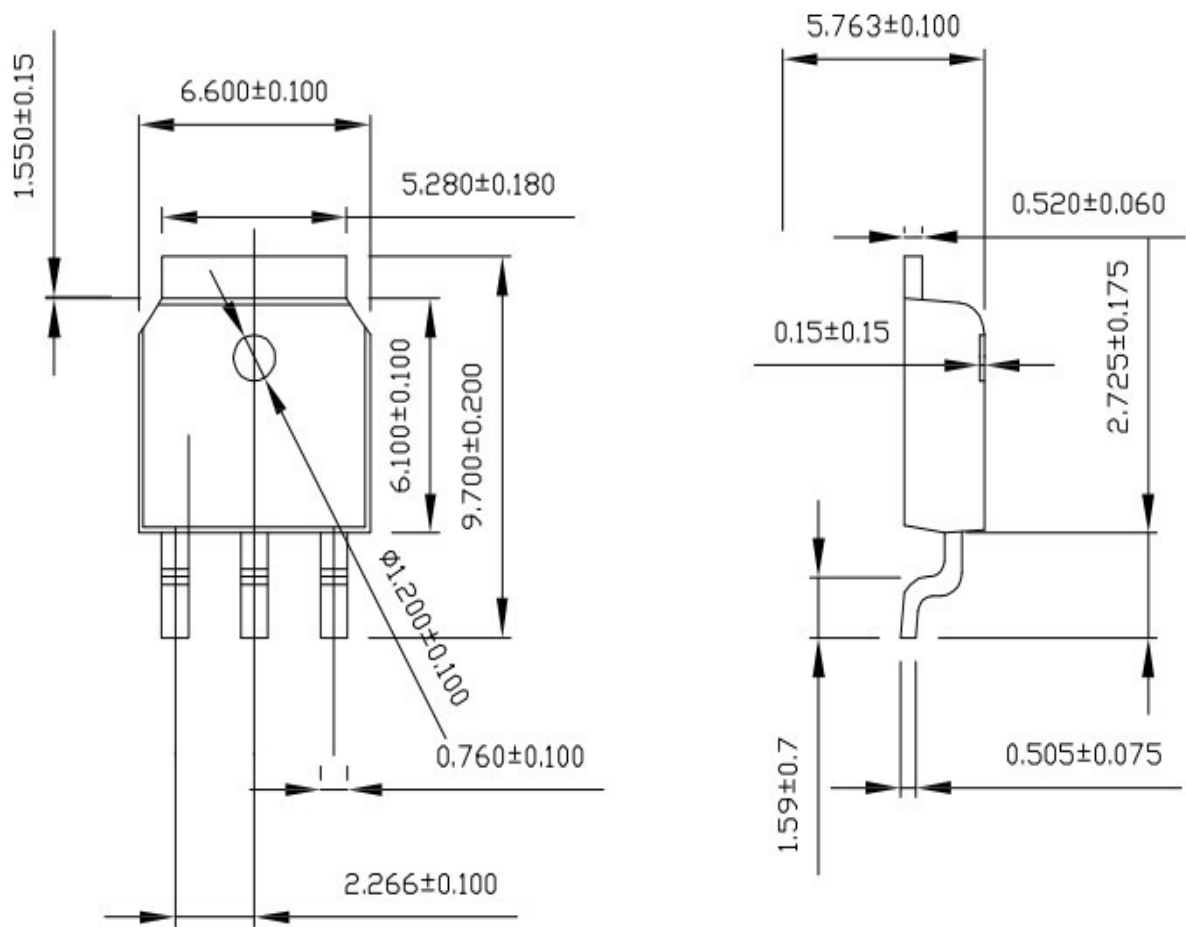
The crunode capacitance curve



Current Derating Curve, Per Element



T0-252



注意事项:
1. XXXX代表日期码, 第一码表示公元年的最后一码, 第二码表示生产时当月码 (A, B, C... 为一月, 二月, 三月...), 第三, 四码表示大量生产时批次码。
例如: 2009年第一月生产的, D/C为9AXX。

MHCHXM

SR1010CS



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修订内容